



High Performance Selectable 1:4 Differential Fanout Buffer

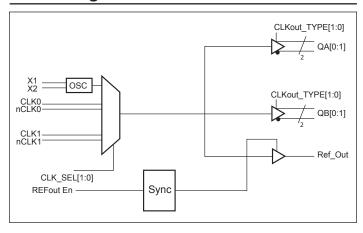
Description

The DIODES PI6C49S1504T is a high-performance fanout buffer device which supports up to 1.5GHz frequency. This device is ideal for systems that need to distribute low-jitter clock signals to multiple destinations.

Application(s)

- Networking Systems, including Switches and Routers
- High-Frequency Backplane-based Computing and Telecom Platforms

Block Diagram



Features

- 4 Differential Outputs with 2 Banks
- User-Configurable Output Signaling Standard for Each Bank: LVDS or LVPECL or HCSL
- LVCMOS Reference Output Up to 200MHz
- Up to 1.5GHz Output Frequency for Differential Outputs
- Ultra-Low Additive Phase Jitter: <0.03ps (typical) (Differential 156.25MHz, 12KHz to 20MHz Integration Range)
- Selectable Reference Inputs Support Either Single-Ended or Differential or Xtal
- Low Skew Between Outputs Within Banks (<40ps)
- Low Delay from Input to Output (Tpd typical <1.5ns)
- Separate Input Output Supply Voltage for Level Shifting
- 2.5V/3.3V Power Supply
- Industrial Temperature Support
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green):
 - □ 32-pin, TQFN (ZH)

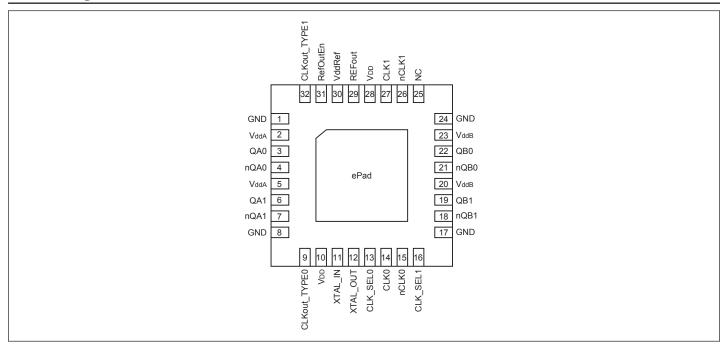
Notes

- $1.\ No\ purposely\ added\ lead.\ Fully\ EU\ Directive\ 2002/95/EC\ (RoHS),\ 2011/65/EU\ (RoHS\ 2)\ \&\ 2015/863/EU\ (RoHS\ 3)\ compliant.$
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





Pin Configuration



Pin Description

Pin #	Pin Name	Type	Description
1, 8, 17, 24	GND	Power	Negative power supply.
25	NC	-	Not Connect.
2,5	$V_{\rm ddA}$	Power	Power supply for Bank A Output buffers. V_{ddA} operates from 3.3V or 2.5V.
13	CLK_SEL0	Input	Clock input source selection pin. Has internal pull down.
16	CLK_SEL1	Input	Clock input source selection pin. Has internal pull down.
14,	CLK0	Input	Differential clock input has internal pull up/down in DC offset.
15	nCLK0	Input	Differential clock input has internal pull up/down in DC offset.
27,	CLK1	Input	Differential clock input has internal pull up/down in DC offset.
26	nCLK1	Input	Differential clock input has internal pull up/down in DC offset.
11	XTAL_In	Input	Input for crystal, XO, or single ended clock.
12	XTAL_Out	Output	Output for crystal. Leave Xtal_Out floating if Xtal_In is driven by a single ended clock.
10, 28	V_{DD}	Power	Power supply for core.
18,	nQB1	Outmut	Differential output alordy
19	QB1	Output	Differential output clock.
21,	nQB0	Output	Differential output clock.
22	QB0	Output	Differential output clock.





Pin #	Pin Name	Туре	Description
29	Ref_Out	Output	Reference output clock.
7,	nQA1	Outmut	Differential output alords
6	QA1	Output	Differential output clock.
4,	nQA0	Outmut	Differential output alords
3	QA0	Output	Differential output clock.
9	CLKout_TYPE0	Input	Bank A and bank B output buffer type selection pins. Has internal pull down.
32	CLKout_TYPE1	Input	Bank A and bank B output buffer type selection pins. Has internal pull down.
ePad	ePad	GND	Connect to the PCB ground.
20, 23	$V_{ m ddB}$	Power	Power supply for Bank B Output buffers. V_{ddB} operates from 3.3V or 2.5V.
30	VddRef	Power	Power supply for reference clock output.
31	RefOutEn	Input	REFout enable pin. Has internal pull down.





Function Table

Table 1: Input Selection

CLK_SEL1	CLK_SEL0	Selected Input
0	0	CLK0, nCLK0
0	1	CLK1, nCLK1
1	X	XTAL_In

Table 2: Differential Output Buffer Type Selection

CLKout_TYPE1	CLKout_TYPE0	CLKoutX Buffer Type (Bank A and B)
0	0	LVPECL
0	1	LVDS
1	0	HCSL
1	1	Disabled (Hi-Z)

Table 3: Reference Output Enable

REFout_EN	REFout STATE
0	Disabled (Hi-Z)
1	Enabled

Table 4: CLKx Input vs. Output States

State of Selected Input Clock	State of Enabled Outputs
CLKx and nCLKx Inputs Floating	Logic Low
CLKx and nCLKx Inputs Shorted Together	Not Supported. Output is Undefined
CLKx Logic Low	Logic Low
CLKx Logic High	Logic High





Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested)

Note

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Power Supply Characteristics and Operating Conditions

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V_{DD}	Core Supply Voltage		2.375		3.465	V
V_{DDO}	Output Supply Voltage	$V_{DDO} \le V_{DD}$	2.375		3.465	V
		All LVPECL Loaded		45	65	
I_{DD}	Core Power Supply Current	All LVDS Loaded		50	65	
		All HCSL Loaded		50	45	mA
		All LVPECL Loaded		140	180	
I_{DDO}	Output Power Supply Current	All LVDS Loaded		35	46	
		All HCSL Loaded		90	125	
T_{A}	Ambient Operating Temperature ⁽¹⁾		-40		85	°C

Note:

DC Electrical Specifications - Differential Inputs

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I_{IH}	Input High current	$Input = V_{DD}$			150	uA
I_{IL}	Input Low current	Input = GND	-150			uA
C_{IN}	Input capacitance			3		PF
V_{IH}	Input high voltage				V _{DD} +0.3	V
V_{IL}	Input low voltage		-0.3			V
$ m V_{ID}$	Input Differential Amplitude PK-PK		0.15		1.3	V
V_{CM}	Common model input voltage		0.25		V _{DD} -1.2	V
ISO _{MUX}	MUX isolation			-89		dBc

^{1.} Either T_A or T_B used as operating condition





DC Electrical Specifications - LVCMOS Inputs

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
I_{IH}	Input High current	$Input = V_{DD}$			150	uA
I _{IL}	Input Low current	Input = GND	-150			uA
V _{IH}	Input high voltage	$V_{DD} = 3.3V$	2.0		V _{DD} +0.3	V
V _{IL}	Input low voltage	$V_{DD} = 3.3V$	-0.3		0.8	V
V _{IH}	Input high voltage	$V_{DD} = 2.5V$	1.7		V _{DD} +0.3	V
V _{IL}	Input low voltage	$V_{DD} = 2.5V$	-0.3		0.7	V

DC Electrical Specifications- LVPECL Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{OH}	Output High voltage		V _{DDO} -1.4		V _{DDO} -0.9	V
V _{OL}	Output Low voltage		V _{DDO} -2.2		V _{DDO} -1.7	V

DC Electrical Specifications- LVDS Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{OH}	Output High voltage		1.4	1.5	1.6	V
V _{OL}	Output Low voltage		1	1.1	1.25	V
Vocm	Output commode voltage		1.2	1.3	1.45	V
DVocm	Change in Vocm between completely output states				50	mV
Ro	Output impedance		85		140	W

DC Electrical Specifications – HCSL Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{OH} Output High voltage	2.5V	660	725	850	mV	
	Output High voltage	3.3V	700	850	900	mV
V_{OL}	Output Low voltage		-150		150	mV

DC Electrical Specifications – LVCMOS Output

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{OH} Output High voltage	0 4 417 1 16	$V_{\rm DDO} = 3.3 V + /-5\%, I_{\rm OH} = -8 mA$	2.3			V
	Output High voltage	$V_{\rm DDO} = 2.5 V$ +/- 5%, $I_{\rm OH} = -8 m A$	1.5			V





Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{OL}	Output Low voltage	$V_{\rm DDO} = 3.3 \text{V} + /-5\%, I_{\rm OL} = 8 \text{mA}$			0.5	V
		$V_{\rm DDO} = 2.5 V + /-5\%, I_{\rm OL} = 8 m A$			0.4	V
V _{OH}	Output High voltage	$V_{\rm DDO} = 3.3 V + /-5\%, I_{\rm OH} = -24 mA$	2.1			V
		$V_{\rm DDO} = 2.5 V$ +/- 5%, $I_{\rm OH} = -16 m A$	1.5			V
V _{OL}	Output Low voltage	$V_{\rm DDO} = 3.3 V$ +/-5%, $I_{\rm OL} = 24 mA$			1	V
		$V_{\rm DDO} = 2.5 \text{V}$ +/- 5%, $I_{\rm OL} = 16 \text{mA}$			0.8	V

AC Electrical Specifications – Differential Outputs

Parameter	Description	Conditions	Conditions		Typ.	Max.	Units
Б	Clock output frequency	LVPECL, LVDS				1500	2411
F_{OUT}		HCSL				250	MHz
	Output rise time		LVPECL	100	150	300	ps
$T_{\rm r}$		From 20% to 80%	LVDS	100	150	300	
			HCSL	300		700	
			LVPECL	100	150	300	
$T_{\rm f}$	Output fall time	From 80% to 20%	LVDS	100	150	300	ps
			HCSL	300		700	
	Output duty cycle	Frequency $<$ 650MHz, $V_{ID} \ge$	LVPECL, HCSL (<250MHz)	48		52	%
		400mV	LVDS	47		53	
т		Frequency < 1GHz, $V_{ID} \ge 400 \text{mV}$	LVPECL	45		55	
$T_{ m ODC}$			LVDS	45		55	
		Frequency $< 1.5 GHz$, $V_{ID} \ge 400 mV$	LVDS	40		60	
		Frequency $< 1.5 GHz$, $V_{ID} \ge 400 mV$	LVPECL	40		60	
		LVPECL outputs @ <	1GHz	500		1100	mV
3.7		LVPECL outputs @ >	1GHz	400		1000	
V_{pp}	Output swing Single-ended	LVDS outputs @ <1G	Hz	250		600	
		LVDS outputs @ >1G	LVDS outputs @ >1GHz			550	
T	D. C 11:4: ::44 DMC	156.25MHz, 12kHz to	20MHz		0.02		ps
T_j	Buffer additive jitter RMS	156.25MHz, 10kHz to	1MHz		0.01		ps
V _{CROSS}	Absolute crossing voltage	HCSL			460		mV
DV _{CROSS}	Total variation of crossing voltage	HCSL				140	mV





Parameter	Description	Conditions	Min.	Тур.	Max.	Units
T_{sk}	Output Skew	4 outputs devices, outputs in same bank, with same load, at DUT.		15	40	ps
T_{PD}	Propagation Delay	LVPECL, LVDS @ 3.3V, 100MHz		570		ps
		HCSL @ 3.3V, 100MHz		900		ps
T _{OD}	Valid to HiZ				200	ns
T _{OE}	HiZ to valid				200	ns
T _{P2P Skew}	Part to Part Skew(1)			80	120	ps

AC Electrical Specifications – CMOS

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
Г	D.C. C.	XTAL input	10		50	MHz
F_{OUT}	Ref_Out frequency	Reference input			200	MHz
T.	D 6 11:0 11:0 D160	XTAL input		0.3		ps
T_{j}	Buffer additive jitter RMS	Reference input		0.03		ps
$t_{\rm r/}t_{\rm f}$	Rise time, Fall time	$C_L = 5pF$		0.8		ns
		$C_L = 5pF$				
T_{ODC}	Output duty cycle	3.3V, max test freq. 250MHz	45		55	%
		2.5V, max test freq. 150MHz				
t_{PD}	Propagation delay	3.3V, 25MHz		4500		ps
t_{s}	Setup time		300			ps
t_{SOD}	Clock edge to output disable	Ref_Out	2		4	cycles
t _{SOE}	Clock edge to output enable	Ref_Out	2		4	cycles
_	0 4 4 1	$V_{DDO} = 3.3V \pm 5\%$		30		Ω
R_{IUT}	Output Impedance	$V_{\rm DDO} = 2.5 V \pm 5\%$		45		Ω

Notes:

1. This parameter is guaranteed by design





Crystal Characteristics

Parameter	Min.	Typ.	Max.	Units
Mode of Oscillation		Fundamental		
Frequency Range	10		50	MHz
Equivalent Series Resistance (ESR)			70	Ω
Shunt Capacitance			7	pF
Load Capacitance	10		18	pF
Drive Level			500	μW

Recommended Crystals

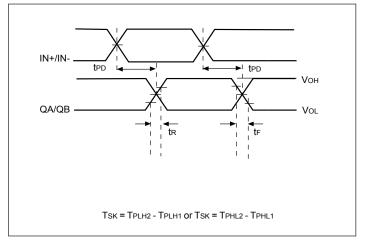
Diodes Recommends:

- a) GC2500003 XTAL 49S/SMD(4.0 mm), 25M, CL=18pF, +/-30ppm http://www.pericom.com/pdf/datasheets/se/GC_GF.pdf
- b) FY2500091, SMD 5x3.2(4P), 25M, CL=18pF, +/-30ppm http://www.pericom.com/pdf/datasheets/se/FY_F9.pdf
- c) FL2500047, SMD 3.2x2.5(4P), 25M, CL=18pF, +/-20ppm http://www.pericom.com/pdf/datasheets/se/FL.pdf

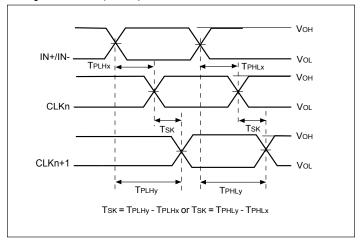




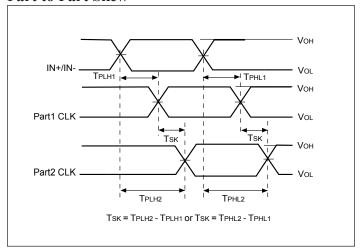
Propagation Delay (TPD)



Output Skew (TSK)



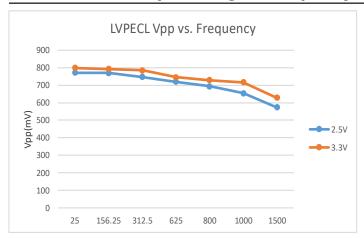
Part to Part Skew

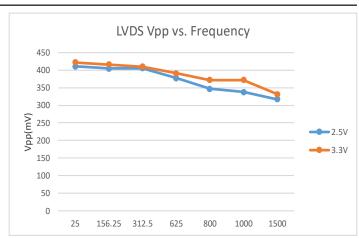




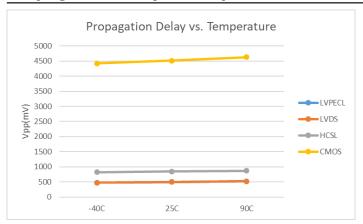


LVPECL/ LVDS Output Swing vs. Frequency



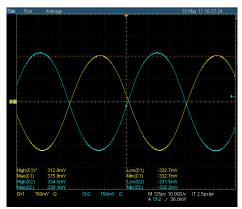


Propagation Delay vs Temperature

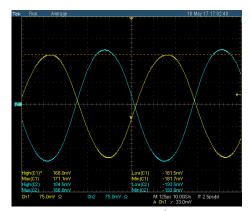




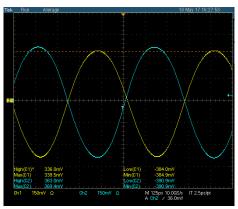
1.5GHz LVPECL/ LVDS Waveform



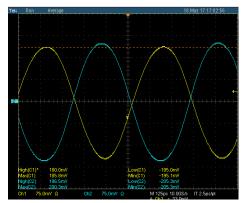
2.5V LVPECL Waveform



2.5V LVDS Waveform



3.3V LVPECL Waveform



3.3V LVDS Waveform



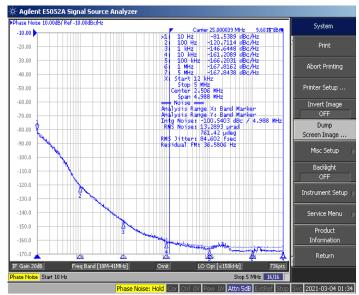


Phase Noise and Additive Jitter

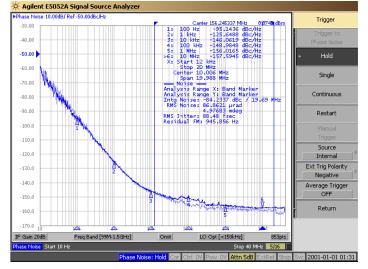
Output phase noise (Dark Blue) vs Input Phase noise (light blue)

Additive jitter is calculated at 25MHz ~71fS RMS (12kHz to 5MHz). Additive jitter = $\sqrt{\text{(Output jitter}^2 - Input jitter}^2)}$

Ref_out 25MHz Phase Noise Plot, VDD = VDDO = 3.3V, 25°C, Driven by 25MHz CMOS XO

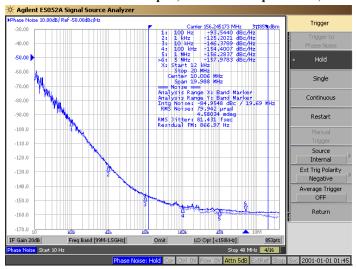


156.25M LVDS Output Additive Jitter Noise Plot, 3.3V



3.3V LVDS Output Jitter 88fs vs. Input 72fs

156.25M LVPECL XO Input, LVPECL output Noise, 3.3V

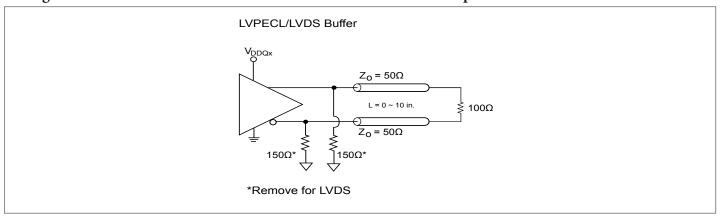


 $3.3 V\ 156.25 M\ LVPECL$ Input LVPECL output Jitter 81fs vs. input jitter 75fs

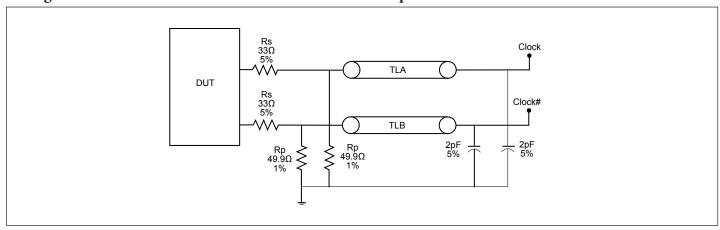




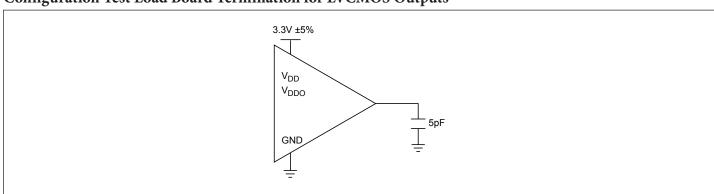
Configuration Test Load Board Termination for LVPECL/ LVDS Outputs



Configuration Test Load Board Termination for HCSL Outputs



Configuration Test Load Board Termination for LVCMOS Outputs







Application Information

Wiring the differential input to accept single ended levels

Figure 1 shows how the differential input can be wired to accept single ended levels. The reference voltage $V_REF = V_{DD}/2$ is generated by the bias resistors R1, R2 and C1. This bias circuit should be located as close as possible to the input pin. The ratio of R1 and R2 might need to be adjusted to position the V_REF in the center of the input voltage swing. For example, if the input clock swing is only 2.5V and $V_{DD} = 3.3$ V, V_REF should be 1.25V and R2/R1 = 0.609.

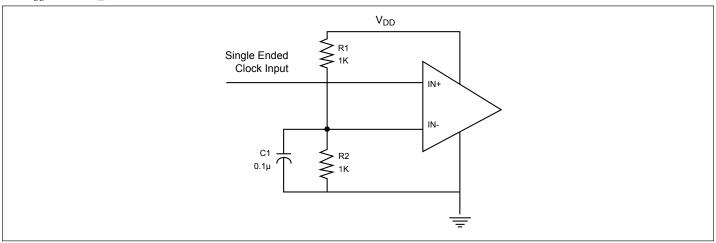
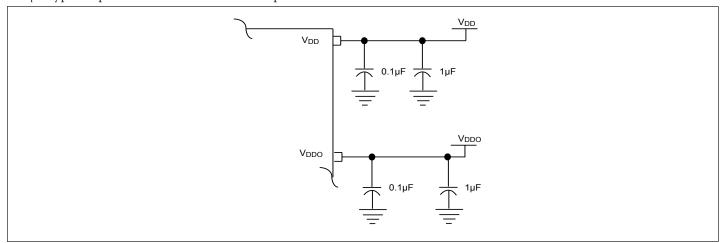


Figure 1. Single-ended Input to Differential Input Device

Power Supply Filtering Techniques

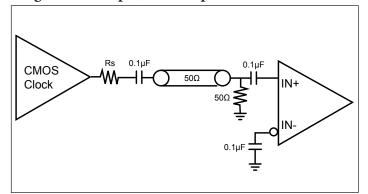
As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. All power pins should be individually connected to the power supply plane through vias, and $0.1\mu F$ an $1\mu F$ bypass capacitors should be used for each pin.



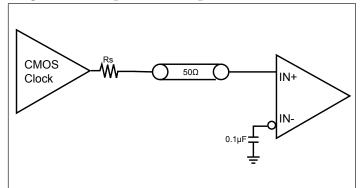




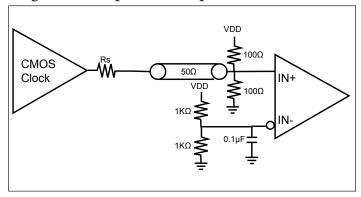
Single Ended Input, AC Couple



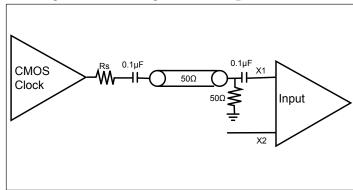
Single Ended Input, DC Couple



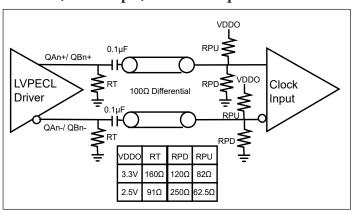
Single Ended Input, DC Couple



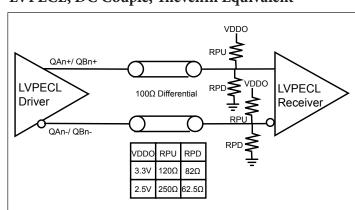
Driving X1 with a Single Ended Input



LVPECL, AC Couple, Thevenin Equivalent



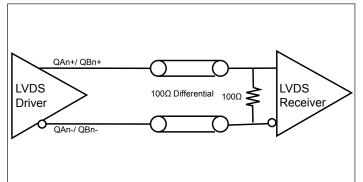
LVPECL, DC Couple, Thevenin Equivalent



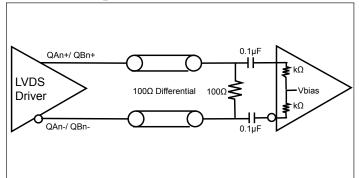




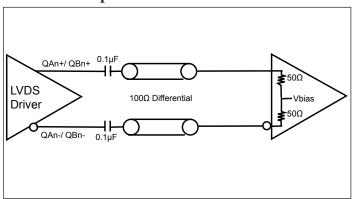
LVDS DC Couple



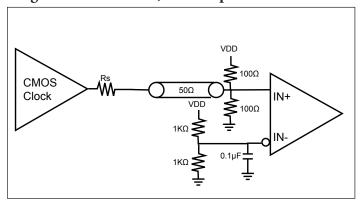
LVDS AC Couple at Load



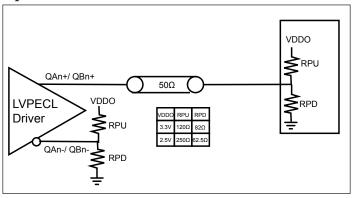
LVDS AC Couple with Internal Termination



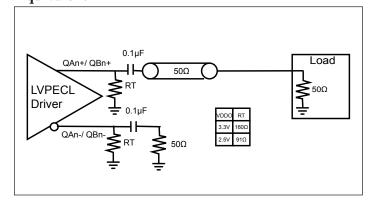
Single Ended LVPECL, DC Couple



Single Ended LVPECL, DC Couple, Thevenin Equivalent



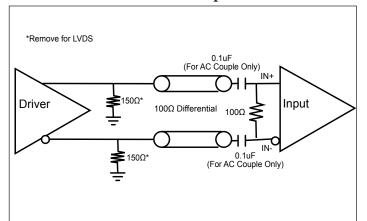
Single Ended LVPECL, AC Couple, Thevenin Equivalent



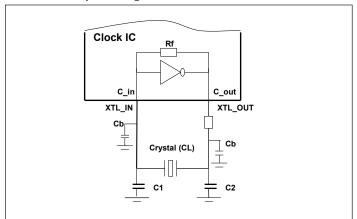




LVPECL/ LVDS AC and DC Input



Clock IC Crystal Input Guide



Part Marking

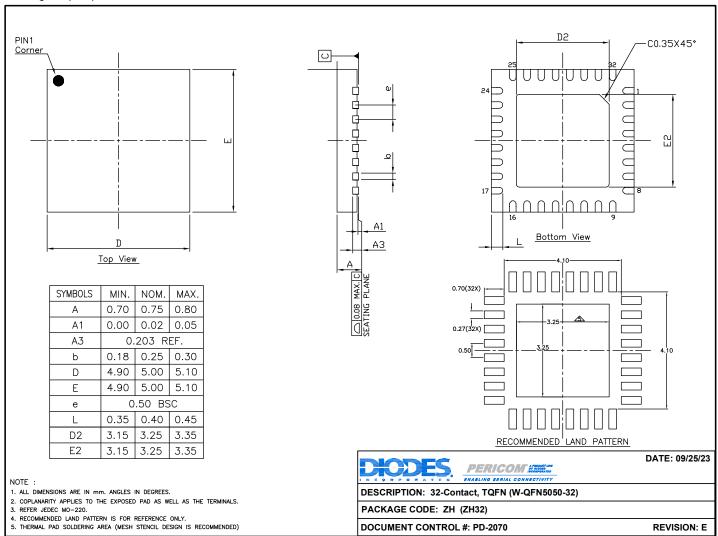
Top mark not available at this time. To obtain advance information regarding the top mark, please contact your local sales representative.





Packaging Mechanical

32-TQFN (ZH)



For latest package info.

 $please\ check:\ http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/packaging-mechanical-and-thermal-characteristics/packaging-mech$

Ordering Information

Ordering Code	Package Code	Package Description	Operating Temperature
PI6C49S1504TZHIEX	ZH	32-Pin, W-QFN5050-32	-40 °C to 85 °C

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. I = Industrial
- 5. E = Pb-free and Green
- 6. X suffix = Tape/Reel





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